

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	("4392362").PN.	US-PGPUB; USPAT	OR	OFF	2005/07/21 17:26
L2	29	((("6344116") or ("4881257") or ("4902897") or ("4516148") or ("5920013") or ("4330596") or ("5333505") or ("6214691") or ("6214691") or ("5476819") or ("5503285") or ("5840199") or ("5850042") or ("4609968") or ("5528452") or ("5585311") or ("5824204") or ("6195214") or ("4261086") or ("4386453") or ("4539278") or ("4574327") or ("4578735") or ("4608268") or ("4632871") or ("4773972") or ("4825335") or ("4916497") or ("4939052") or ("4978421"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/07/21 17:31
L3	709543	silicon	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:31
L4	40475	borosilicate pyrex	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:31
L5	28	L2 and L3 and L4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:31
L6	3536639	ions field	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:31
L7	19	5 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:31
L8	2170214	diameter	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:31
L9	12	7 and 8	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:44
L10	1371390	channel channels	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:32

L11	17750	8 near3 10	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:32
L12	1	9 and 11	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:32
L13	5020473	aluminum al	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:45
L14	4384151	gold au	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:44
L15	12	9 and (13 or 14)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:45
L16	920175	aluminum	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:45
L17	8	9 and (16 or 14)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:46
L18	19	2 and (16 or 14)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:51
L19	3	((("6803840") or ("6286226") or ("6465132"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/07/21 17:52
L22	4	(US-4467394-\$ or US-5644395-\$ or US-6458325-\$ or US-5824204-\$). did.	USPAT	OR	OFF	2005/07/21 17:57
L23	2	22 and (16 or 14)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:59
L24	898	field adj assisted	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00
L25	5772	dangling adj (bond bonds)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00

L26	972311	silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00
L27	44803	borosilicate pyrex	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00
L28	870	(24 or 25) and 26 and 27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00
L29	781283	channels	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00
L30	91	28 and 29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00
L31	71	30 and (16 or 14)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00
L32	1674654	inlet outlet	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:00
L33	1727308	inlet inlets outlet outlets	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:01
L34	46572	29 with 33	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:01
L35	7	31 and 34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:05

L36	5182	29 with (16 or 14)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:05
L37	7	28 and 36	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:06
L38	1533733	semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:06
L39	707629	electronics	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:07
L40	2535	38 near2 39	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:07
L43	4	28 and 40	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:14
L44	1	("5690763").PN.	US-PGPUB; USPAT	OR	OFF	2005/07/21 18:22
L45	164984	cryogenic refrigerator refrigeration	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:16
L46	286	45 and 36	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:16
L47	357495	micro minature nano	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:16
L48	32	46 and 47	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:20

L49	0	44 and (14 or 16)	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:20
L50	3108507	advantage benefit cooling conduct conducting	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:22
L51	340	36 with 50	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:23
L52	37	46 and 51	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:34
L53	32	52 not 48	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:26
L54	0	53 and 3 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:26
L55	37	45 and 51	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:35
L56	0	55 not 52	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:35
L58	286	45 and 36	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:36
L59	251	50 and 58	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:36
L60	32	47 and 58	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:36
L61	32	60 not 53	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 18:39

L62	2	de-3926466-\$.did.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2005/07/21 18:39
L63	1	1991-052118.NRAN.	DERWENT	OR	OFF	2005/07/21 18:39
S1	1	("4392362").PN.	USPAT; USOCR	OR	OFF	2004/12/11 17:30
S2	333042	silicon	USPAT	OR	OFF	2005/07/21 17:26
S3	545321	glass	USPAT	OR	OFF	2004/06/11 18:12
S4	106278	wafer	USPAT	OR	OFF	2004/06/11 18:12
S5	30371	silicon near wafer	USPAT	OR	OFF	2004/06/11 18:13
S6	996650	deposit deposited layer layered	USPAT	OR	OFF	2004/06/11 18:13
S7	668	glass with (silicon near wafer) with (deposit deposited layer layered)	USPAT	OR	OFF	2004/06/11 18:20
S8	675571	reactor reaction	USPAT	OR	OFF	2004/06/11 18:14
S9	247	(glass with (silicon near wafer) with (deposit deposited layer layered)) and (reactor reaction)	USPAT	OR	OFF	2004/06/11 18:20
S10	287903	channels	USPAT	OR	OFF	2004/06/11 18:14
S11	24	((glass with (silicon near wafer) with (deposit deposited layer layered)) and (reactor reaction)) and channels	USPAT	OR	OFF	2004/06/11 18:20
S12	21	("4708600" "4822250" "4908112" "5085562" "5171132" "5224843" "5252294" "5451788" "5519635" "5525041" "5611676" "5637469" "5677195" "5705018" "5816780" "5840062" "5856174" "5863502" "5876187" "5922591" "6054277").PN.	USPAT	OR	OFF	2004/06/11 18:18
S13	9522	pyrex	USPAT	OR	OFF	2004/06/11 18:20
S14	30	pyrex with (silicon near wafer) with (deposit deposited layer layered)	USPAT	OR	OFF	2004/06/11 18:20
S15	7	(pyrex with (silicon near wafer) with (deposit deposited layer layered)) and (reactor reaction)	USPAT	OR	OFF	2004/06/11 18:20
S16	6	((pyrex with (silicon near wafer) with (deposit deposited layer layered)) and (reactor reaction)) and channels	USPAT	OR	OFF	2004/06/11 18:21
S17	94	ashmead.in.	USPAT	OR	OFF	2004/06/11 18:21
S18	930744	plate	USPAT	OR	OFF	2004/06/11 18:21
S19	931923	ashmead.in. adn plate	USPAT	OR	OFF	2004/06/11 18:21

S20	8	ashmead.in. and plate	USPAT	OR	OFF	2004/06/11 18:22
S21	2	"field assisted bond"	USPAT	OR	OFF	2004/06/11 18:28
S22	97015	doped	USPAT	OR	OFF	2004/06/11 18:31
S23	67191	intrinsic	USPAT	OR	OFF	2004/06/11 18:31
S24	237639	dioxide	USPAT	OR	OFF	2004/06/11 18:31
S25	476479	aluminum	USPAT	OR	OFF	2004/06/11 18:31
S26	117654	gold	USPAT	OR	OFF	2004/06/11 18:31
S27	709708	electric	USPAT	OR	OFF	2004/06/11 18:31
S28	3	(US-6458325-\$ or US-5644395-\$ or US-4467394-\$).did.	USPAT	OR	OFF	2004/06/11 18:32
S29	0	doped and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$). did.)	USPAT	OR	OFF	2004/06/11 18:32
S30	0	intrinsic and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$). did.)	USPAT	OR	OFF	2004/06/11 18:32
S31	0	dioxide and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$). did.)	USPAT	OR	OFF	2004/06/11 18:32
S32	0	electric and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$). did.)	USPAT	OR	OFF	2004/06/11 18:32
S33	1	aluminum and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$). did.)	USPAT	OR	OFF	2004/06/11 18:33
S34	1	gold and ((US-6458325-\$ or US-5644395-\$ or US-4467394-\$). did.)	USPAT	OR	OFF	2004/06/11 18:36
S35	10832	doped adj silicon	USPAT	OR	OFF	2004/06/11 18:36
S36	741	intrinsic adj silicon	USPAT	OR	OFF	2004/06/11 18:36
S37	1052	wafer with (doped adj silicon)	USPAT	OR	OFF	2004/06/11 18:36
S38	65	wafer with (intrinsic adj silicon)	USPAT	OR	OFF	2004/06/11 18:36
S39	3	(wafer with (doped adj silicon)) and (wafer with (intrinsic adj silicon))	USPAT	OR	OFF	2004/06/11 18:37
S40	62822	silicon adj dioxide	USPAT	OR	OFF	2004/06/11 18:37
S41	4950	wafer with (silicon adj dioxide)	USPAT	OR	OFF	2004/06/11 18:37
S42	458512	coated	USPAT	OR	OFF	2004/06/11 18:37
S43	412	(wafer with (silicon adj dioxide)) with coated	USPAT	OR	OFF	2004/06/11 18:38
S44	225	glass and ((wafer with (silicon adj dioxide)) with coated)	USPAT	OR	OFF	2004/06/11 18:38

S45	29	((("6344116") or ("4881257") or ("4902897") or ("4516148") or ("5920013") or ("4330596") or ("5333505") or ("6214691") or ("6214691") or ("5476819") or ("5503285") or ("5840199") or ("5850042") or ("4609968") or ("5528452") or ("5585311") or ("5824204") or ("6195214") or ("4261086") or ("4386453") or ("4539278") or ("4574327") or ("4578735") or ("4608268") or ("4632871") or ("4773972") or ("4825335") or ("4916497") or ("4939052") or ("4978421"))).PN.	US-PGPUB; USPAT	OR	OFF	2005/07/21 16:18
S46	709543	silicon	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 16:18
S47	40475	borosilicate pyrex	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 16:18
S48	28	S45 and S46 and S47	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 17:31
S49	11016	dangling	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 16:19
S50	0	S48 and S49	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 16:19
S51	113173	template	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 16:19
S52	0	S48 and S51	US-PGPUB; USPAT; USOCR; EPO; JPO	OR	OFF	2005/07/21 16:19

10067167_CLS
Most Frequently Occurring Classifications of Patents Returned
From A Search of 10067167 on July 21, 2005

Original Classifications

3 216/2
3 361/283.4
2 29/25.41
2 430/5
2 438/400

Cross-Reference Classifications

3 73/718
3 73/724
3 338/4
2 29/621.1
2 156/272.2
2 250/505.1
2 257/419
2 257/E21.546
2 361/278
2 361/279
2 361/283.1
2 361/283.4
2 378/35
2 430/967
2 438/221
2 438/424
2 438/456
2 438/51
2 438/52

Combined Classifications

5 361/283.4
4 216/2
3 29/25.41
3 73/718
3 73/724
3 338/4
3 378/35
3 430/5
3 438/456
2 29/621.1
2 156/272.2
2 250/505.1
2 257/419
2 257/E21.546
2 361/278
2 361/279
2 361/283.1
2 430/967
2 438/221
2 438/400
2 438/424
2 438/51
2 438/52

10067167_CLSTITLES
Titles of Most Frequently Occurring Classifications of Patents Returned
From A Search of 10067167 on July 21, 2005

- 5 361/283.4 (3 OR, 2 XR)
Class 361 : ELECTRICITY: ELECTRICAL SYSTEMS AND DEVICES
361/271 ELECTROSTATIC CAPACITORS
361/277 .Variable
361/280 ..Responsive to external condition
361/283.1 ...Pressure
361/283.4By diaphragm
- 4 216/2 (3 OR, 1 XR)
Class 216 : ETCHING A SUBSTRATE: PROCESSES
216/2 ETCHING OF SEMICONDUCTOR MATERIAL TO PRODUCE AN
ARTICLE HAVING A NONELECTRICAL FUNCTION
- 3 29/25.41 (2 OR, 1 XR)
Class 029 : METAL WORKING
29/25.41 ELECTRIC CONDENSER MAKING
- 3 73/718 (0 OR, 3 XR)
Class 073 : MEASURING AND TESTING
73/700 FLUID PRESSURE GAUGE
73/715 .Diaphragm
73/716 ..Multiple and/or differential
73/717 ...With electrical readout
73/718Capacitive
- 3 73/724 (0 OR, 3 XR)
Class 073 : MEASURING AND TESTING
73/700 FLUID PRESSURE GAUGE
73/715 .Diaphragm
73/723 ..With electrical readout
73/724 ...Capacitive
- 3 338/4 (0 OR, 3 XR)
Class 338 : ELECTRICAL RESISTORS
338/2 STRAIN -GAUGE TYPE
338/4 .Fluid- or gas pressure-actuated
- 3 378/35 (1 OR, 2 XR)
Class 378 : X-RAY OR GAMMA RAY SYSTEMS OR DEVICES
378/1 SPECIFIC APPLICATION
378/34 .Lithography
378/35 ..Pattern mask
- 3 430/5 (2 OR, 1 XR)
Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF
430/4 RADIATION MODIFYING PRODUCT OR PROCESS OF
MAKING
430/5 .Radiation mask
- 3 438/456 (1 OR, 2 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
438/455 BONDING OF PLURAL SEMICONDUCTOR SUBSTRATES
438/456 .Having enclosed cavity
- 2 29/621.1 (0 OR, 2 XR)
Class 029 : METAL WORKING

10067167_CLSTITLES

29/592 METHOD OF MECHANICAL MANUFACTURE
 29/592.1 .Electrical device making
 29/610.1 ..Resistor making
 29/621.1 ...Strain gauge making

2 156/272.2 (0 OR, 2 XR)
 Class 156 : ADHESIVE BONDING AND MISCELLANEOUS CHEMICAL
 MANUFACTURE
 156/1 METHODS
 156/60 .Surface bonding and/or assembly therefor
 156/272.2 ..With direct application of electrical,
 magnetic, or radiant energy to work

2 250/505.1 (0 OR, 2 XR)
 Class 250 : RADIANT ENERGY
 250/505.1 RADIATION CONTROLLING MEANS

2 257/419 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/414 RESPONSIVE TO NON-ELECTRICAL SIGNAL (E.G.,
 CHEMICAL, STRESS, LIGHT, OR MAGNETIC FIELD SENSORS)
 257/415 .Physical deformation
 257/417 ..Strain sensors
 257/418 ...With means to concentrate stress
 257/419With thinned central active portion of
 semiconductor surrounded by thick insensitive portion

(e.g.

diaphragm type strain gauge)

2 257/E21.546 (0 OR, 2 XR)
 Class 257 : ACTIVE SOLID-STATE DEVICES
 257/E21.531 ...For electrical parameters, e.g.,
 resistance, deep-levels, CV, diffusions by
 electrical means
 (EPO)
 257/E21.532 .Manufacture or treatment of devices
 consisting of plurality of solid-state components
 formed in
 or on common substrate or of parts thereof;
 manufacture of
 integrated circuit devices or of parts thereof (EPO)
 257/E21.536 ..Manufacture of specific parts of devices
 (EPO)
 257/E21.54 ...Making of isolation regions between
 components (EPO)
 257/E21.545Dielectric regions, e.g., EPIC dielectric
 isolation, LOCOS; trench refilling techniques, SOI
 technology, use of channel stoppers (EPO)
 257/E21.546Using trench refilling with dielectric
 materials (EPO)

2 361/278 (0 OR, 2 XR)
 Class 361 : ELECTRICITY: ELECTRICAL SYSTEMS AND DEVICES
 361/271 ELECTROSTATIC CAPACITORS
 361/277 .Variable
 361/278 ..With significant electrode or terminal
 feature

2 361/279 (0 OR, 2 XR)
 Class 361 : ELECTRICITY: ELECTRICAL SYSTEMS AND DEVICES
 361/271 ELECTROSTATIC CAPACITORS

10067167_CLSTITLES

- 361/277 .Variable
361/279 ..Gas or vacuum dielectric
- 2 361/283.1 (0 OR, 2 XR)
Class 361 : ELECTRICITY: ELECTRICAL SYSTEMS AND DEVICES
- 361/271 ELECTROSTATIC CAPACITORS
361/277 .Variable
361/280 ..Responsive to external condition
361/283.1 ...Pressure
- 2 430/967 (0 OR, 2 XR)
Class 430 : RADIATION IMAGERY CHEMISTRY: PROCESS,
COMPOSITION, OR PRODUCT THEREOF
- 430/966 X-RAY
430/967 .X-ray exposure process
- 2 438/221 (0 OR, 2 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY
FORMATION OR
ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
- 438/197 .Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)
- 438/199 ..Complementary insulated gate field effect
transistors (i.e., CMOS)
- 438/218 ...Including isolation structure
- 438/221Dielectric isolation formed by grooving and
refilling with dielectric material
- 2 438/400 (2 OR, 0 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/400 FORMATION OF ELECTRICALLY ISOLATED LATERAL
SEMICONDUCTIVE STRUCTURE
- 2 438/424 (0 OR, 2 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/400 FORMATION OF ELECTRICALLY ISOLATED LATERAL
SEMICONDUCTIVE STRUCTURE
- 438/424 .Grooved and refilled with deposited dielectric
material
- 2 438/51 (0 OR, 2 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/48 MAKING DEVICE OR CIRCUIT RESPONSIVE TO
NONELECTRICAL SIGNAL
- 438/50 .Physical stress responsive
- 438/51 ..Packaging (e.g., with mounting,
encapsulating, etc.) or treatment of packaged
semiconductor
- 2 438/52 (0 OR, 2 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/48 MAKING DEVICE OR CIRCUIT RESPONSIVE TO
NONELECTRICAL SIGNAL
- 438/50 .Physical stress responsive
- 438/52 ..Having cantilever element

above 3
abstract 1
accommodate 1
according 4
active 1
addition 2
adherence 2
after 2
again 3
alcohol 2
aligned 1
all 1
allow 1
allowed 1
along 2
also 13
alternate 1
alternate 2
alternative 1
aluminum 2
ambient 1
an 17
and 89
angle 1
angles 1
angstroms 1
another 5
any 4
apertures 3
application 1
applied 2
applying 1
appropriate 1
are 36
area 3
areas 11
array 1
arsenide 2
art 1
article 2
as 35
ascertain 2
aspect 1
assisted 7
associated 1
at 16
atmosphere 1
attach 1
attached 1
attachment 1
background 1
basic 2
basically 7
basis 1
be 31
been 2
between 9
big 1
biphenyldimine 1
biphenyldithiol 1
bond 6
bonded 13
bonding 5

bonds 7
bottom 6
brvf 1
but 3
by 14
can 31
capable 1
cause 3
causes 1
cavities 1
center 1
centers 2
chamber 4
channel 6
channels 15
chemical 2
chips 1
chmmels 1
chnmber 3
chosen 4
circuit 1
circular 1
cizculate 1
clear 1
co 1
coated 7
components 1
composed 2
composite 3
compounds 2
conducting 2
conductive 1
conductivity 3
conduit 1
conduits 3
configurations 1
connecting 1
consists 13
construction 1
contacts 1
contain 2
containing 2
contains 2
contemplated 1
controlled 1
conventional 1
corresponding 4
couple 1
course 1
covered 3
create 1
creates 1
cro 1
cross 9
crystallographic 2
ctures 1
dangling 8
degenerately 1
depending 1
deposited 3
depressions 2
descdbed 1
descrvtion 2

designated 2
desired 3
detaded 1
developed 1
device 1
devices 12
diagram 1
differing 1
dimensions 1
dinmeter 1
dioxide 2
diphenyls 1
directed 4
direction 2
directions 1
disclosed 1
disclosure 1
discusses 1
disposed 3
doped 3
drain 2
during 3
each 5
edges 1
effect 1
efficient 1
either 4
electdc 2
electric 3
electro 1
electrodes 1
electronic 2
electronics 1
embodiment 2
employed 1
enable 5
enables 1
enabling 2
end 1
enhancing 1
enlarged 4
entitled 1
envisioned 1
essentially 2
etch 1
etching 5
ether 2
event 2
eventually 1
example 3
exception 1
exist 1
exnmple 1
exposed 3
extent 1
extremely 5
fabdcated 1
fabricate 1
fabricated 1
fabrication 3
field 10
fields 4
figklres 1

figtlre 1
figtzre 1
figure 44
figures 9
find 1
flow 3
fluid 10
fluidic 4
fluids 4
for 17
form 9
formec1 1
formed 11
forming 2
from 8
fundnmental 1
fyld 1
gallium 2
gate 2
glass 13
gold 1
grid 2
has 7
have 4
having 7
high 7
higher 1
highly 1
holes 1
horizontal 2
however 1
icular 1
if 1
important 1
in 49
includes 1
indicated 1
inert 1
infancy 1
influence 1
injected 2
injection 1
instance 1
intemal 2
intersection 1
into 4
intrinsic 2
introduced 3
intzoduced 1
invention 7
ion 3
ions 9
is 63
it 9
its 1
january 1
joined 2
junction 1
known 2
knows 1
kul 1
kulit 1
kulite 1

kullte 6
layer 25
layers 13
leave 2
leaving 1
lf 1
like 2
limitations 1
lined 1
linked 1
liquids 1
ln 2
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lnminate 1
local 2
localized 1
localized 12
location 1
lowered 1
lt 3
made 1
main 1
makes 4
manner 2
many 2
matdx 1
matrix 3
may 8
means 2
metal 7
metals 2
micro 3
microfluidics 1
micropipes 8
microtubes 7
migrate 1
migration 1
miniatttre 1
miniature 5
molecular 7
molecule 4
molecules 13
molset 1
more 1
moreover 1
multiple 2
nanoscale 3
nanostructure 1
new 4
ng 1
nlils 1
not 4
noted 1
now 5
number 2
objective 1
obtain 1
obviously 1
occur 2
of 123
offer 1
ofthe 1
old 1

on 11
one 16
opening 1
operate 1
operating 1
or 27
organic 8
orientation 1
oriented 2
other 9
otherwise 1
oxygen 9
page 11
partially 2
particularly 1
path 1
paths 2
payoffs 1
paz 1
pcvention 1
performed 1
pieces 2
pipe 3
pipes 12
place 1
placenaent 1
places 2
plane 1
planes 2
plklrality 1
plurality 1
plus 1
point 4
pointed 2
points 3
portion 3
possible 4
pressure 1
previously 2
proceed 1
process 2
processing 1
processors 1
produce 4
produced 2
products 1
prominent 1
promote 1
proposed 1
provide 5
pump 1
pyrex 43
rather 1
rea 1
reach 2
reaction 19
reactions 4
reactivity 2
rectangular 3
reduced 1
refen 1
refening 4
referring 3

regard 2
relates 1
researchers 1
result 1
right 2
rn 1
room 1
scientific 1
scientists 1
scope 1
second 1
section 3
sectional 1
sections 2
secured 2
see 3
seen 1
selected 2
selective 1
semi 1
semicircular 1
semiconductor 1
separated 3
series 1
shape 2
shapes 1
shaping 1
sharp 4
shown 18
shows 15
side 6
silicon 65
similar 1
sites 1
size 1
small 3
so 7
sodium 9
soluble 1
solvents 1
source 3
spacing 1
specific 3
speed 1
speeds 1
spot 4
stnlcttzre 1
stnlcture 2
stnzcture 2
strong 1
structitre 1
structure 17
structures 2
stzucture 1
such 9
suitable 2
summary 1
surface 3
surfaces 1
synthesis 1
systems 4
take 1
tc 1

te 1
techniques 1
technology 2
temperature 1
template 7
term 1
terminate 1
terminates 1
tewlate 1
than 1
that 15
the 172
their 5
then 1
theoretically 1
there 16
therefore 6
thereon 1
these 6
they 2
thin 3
this 13
thousands 1
three 1
through 10
throughout 1
thus 4
times 1
tiny 1
tip 1
tips 4
tl 1
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tllrough 1
to 95
top 12
totally 2
transistor 2
transport 4
transported 2
try 1
tubes 3
turn 2
two 3
under 2
understand 1
understood 3
unique 3
upon 1
use 10
used 4
uses 1
using 4
utilize 1
utilized 3
utilizes 2
utilizing 3
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valves 1
various 10
varying 3

vertical 5
via 1
viewv 1
view 3
voltage 8
wafer 37
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with 16
within 3
working 1
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